

Silicon NPN Power Transistors

MJ15001

DESCRIPTION

- With TO-3 package
- Complement to type MJ15002
- Wide area of safe operation

APPLICATIONS

- For high power audio,disk head positioners and other linear applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

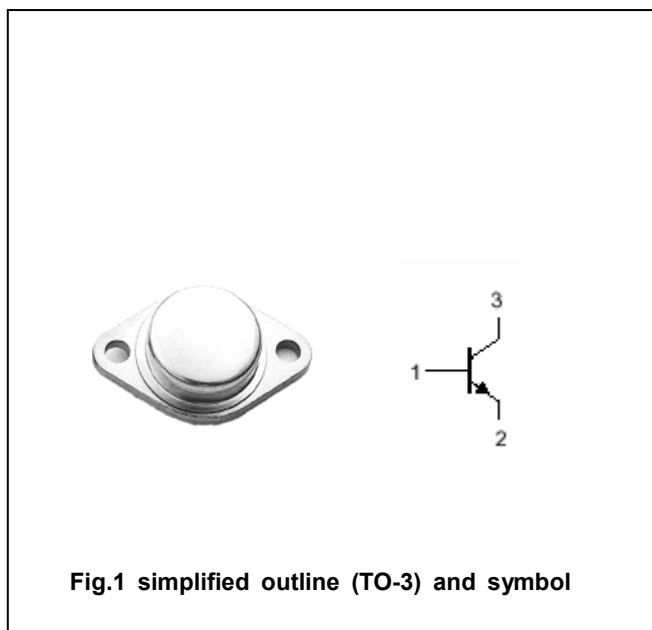


Fig.1 simplified outline (TO-3) and symbol

ABSOLUTE MAXIMUM RATINGS(T_C=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	140	V
V _{CEO}	Collector-emitter voltage	Open base	140	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		15	A
I _B	Base current		5	A
I _E	Emitter current		-20	A
P _D	Total power dissipation	T _C =25℃	200	W
T _j	Junction temperature		200	℃
T _{stg}	Storage temperature		-65~200	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance junction to case	0.875	℃/W

Silicon NPN Power Transistors

MJ15001

CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE(SUS)}	Collector-emitter sustaining voltage	I _C =0.2A ; I _B =0	140			V
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =4A; I _B =0.4A			1.0	V
V _{BE}	Base-emitter on voltage	I _C =4A ; V _{CE} =2V			2.0	V
I _{CEO}	Collector cut-off current	V _{CE} =140V; I _B =0			0.25	mA
I _{CEX}	Collector cut-off current	V _{CE} =140V; V _{BE(off)} =1.5V T _C =150°C			0.1 2.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			0.1	mA
h _{FE}	DC current gain	I _C =4A ; V _{CE} =2V	25		150	
I _{S/b}	Second breakdown collector current With base forward biased	V _{CE} =40Vdc,t=1s, Nonrepetitive	5			A
		V _{CE} =100Vdc,t=1s, Nonrepetitive	0.5			
C _{OB}	Output capacitance	I _E =0 ; V _{CB} =10V;f=1.0MHz			1000	pF
f _T	Transition frequency	I _C =0.5A ; V _{CE} =10V;f=0.5MHz	2			MHz

PACKAGE OUTLINE

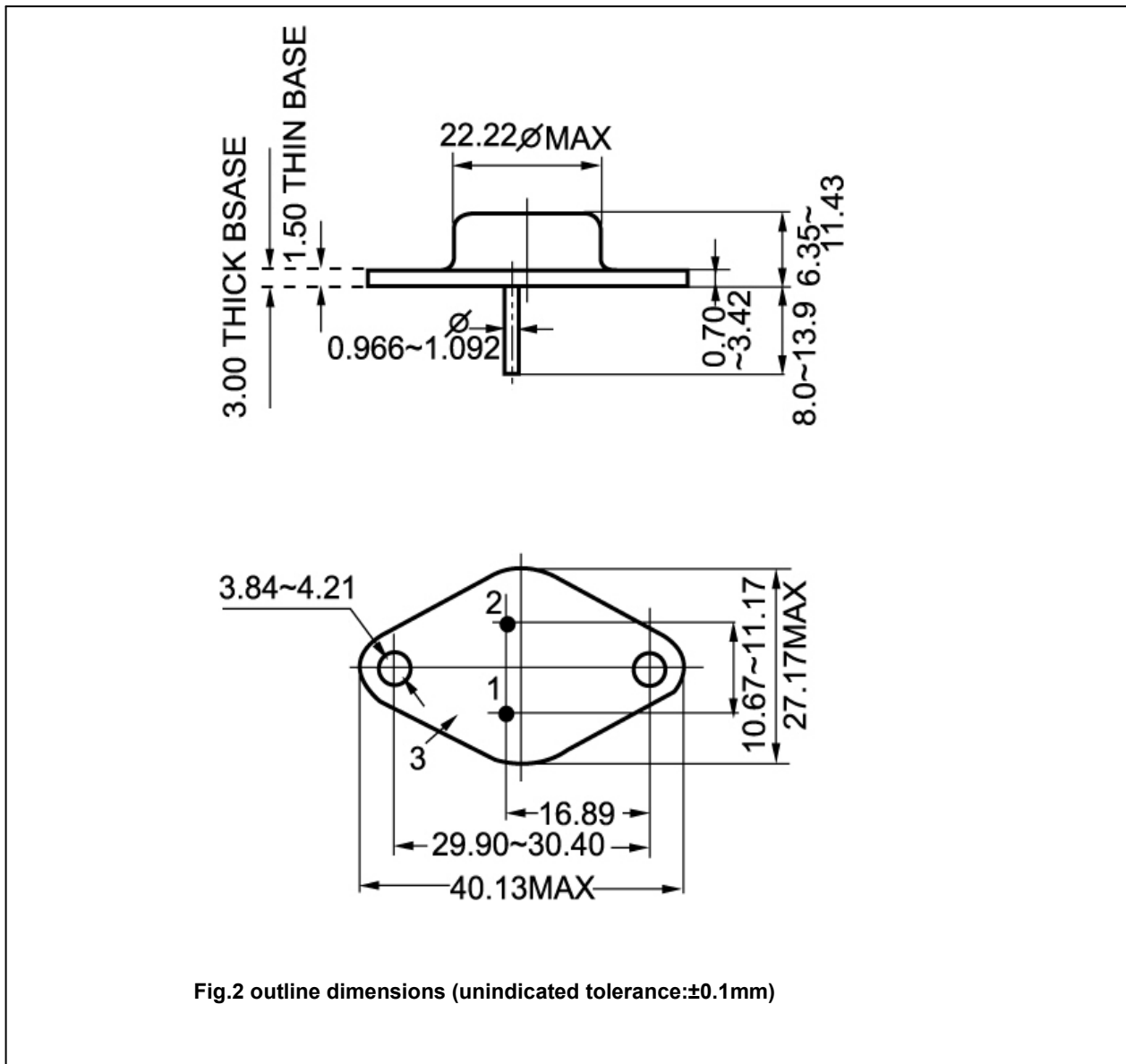


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)